Kochupurackal B Jinesh

List of Publications by Year
in descending order

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		1163117	940533
16	246	8	16
papers	citations	h-index	g-index

16	16	16	397
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Linear Weight Update and Large Synaptic Responses in Neuromorphic Devices Comprising Pulsed-Laser-Deposited BiFeO₃. ACS Applied Electronic Materials, 2022, 4, 592-597.	4.3	6
2	Excitons and Trions in MoS₂ Quantum Dots: The Influence of the Dispersing Medium. ACS Omega, 2022, 7, 6531-6538.	3.5	16
3	Resistive switching in formamidinium lead iodide perovskite nanocrystals: a contradiction to the bulk form. Journal of Materials Chemistry C, 2021, 9, 288-293.	5.5	14
4	Synthesis of nanodiamonds using liquid-phase laser ablation of graphene and its application in resistive random access memory. Carbon Trends, 2021, 3, 100023.	3.0	6
5	Programmable electronic synapse and nonvolatile resistive switches using MoS2 quantum dots. Scientific Reports, 2020, 10, 12450.	3.3	22
6	Vertical limits of resistive memory scaling: The detrimental influence of interface states. Applied Physics Letters, 2020, 116, .	3.3	3
7	Surfactant molecules make liquid phase exfoliated graphene a switching element for resistive random access memory applications. Journal of Materials Science: Materials in Electronics, 2018, 29, 9700-9708.	2.2	2
8	Scaling of resistive random access memory devices beyond 100 nm²: influence of grain boundaries studied using scanning tunneling microscopy. Nanotechnology, 2018, 29, 495202.	2.6	7
9	Consideration of UFET Architecture for the 5 nm Node and Beyond Logic Transistor. IEEE Journal of the Electron Devices Society, 2018, 6, 1129-1135.	2.1	12
10	Raman and scanning tunneling spectroscopic investigations on graphene-silver nanocomposites. Journal of Science: Advanced Materials and Devices, 2018, 3, 353-358.	3.1	13
11	Anisotropic Phase Formation Induced Enhancement of Resistive Switching in Bioâ€“based Imidazolium Ionic Liquid Crystals.. ChemistrySelect, 2017, 2, 315-319.	1.5	4
12	Liquid phase exfoliated graphene for electronic applications. Materials Research Express, 2017, 4, 095017.	1.6	8
13	Gate controllable resistive random access memory devices using reduced graphene oxide. Applied Physics Letters, 2016, 108, .	3.3	12
14	Hybrid Perovskite Nanoparticles for Highâ€Performance Resistive Random Access Memory Devices: Control of Operational Parameters through Chloride Doping. Advanced Materials Interfaces, 2016, 3, 1600092.	3.7	71
15	Facile strategy for the fabrication of efficient nonvolatile bistable memory devices based on polyvinylcarbazoleâ€“zinc oxide. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2414-2424.	1.8	8
16	Resistive switching in polymethyl methacrylate thin films. Organic Electronics, 2016, 29, 33-38.	2.6	42